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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET

PDTA123E series PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

Product data sheet Supersedes data of 2004 Apr 07 2004 Aug 02



PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- · Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | TYP. | MAX. | UNIT |
|-----------|---------------------------|------|------|------|
| V_{CEO} | collector-emitter voltage | _ | -50 | V |
| Io | output current (DC) | _ | -100 | mA |
| R1 | bias resistor | 2.2 | _ | kΩ |
| R2 | bias resistor | 2.2 | _ | kΩ |

DESCRIPTION

PNP resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

| TYPE NUMBER | PAC | KAGE | MARKING CODE | NDN COMPLEMENT | |
|-------------|---------------|--------|--------------------|----------------|--|
| ITPE NUMBER | PHILIPS | EIAJ | MARKING CODE | NPN COMPLEMENT | |
| PDTA123EE | SOT416 | SC-75 | 5C | PDTC123EE | |
| PDTA123EEF | SOT490 | SC-89 | 6C | PDTC123EEF | |
| PDTA123EK | SOT346 | SC-59 | 42 | PDTC123EK | |
| PDTA123EM | SOT883 | SC-101 | F7 | PDTC123EM | |
| PDTA123ES | SOT54 (TO-92) | SC-43 | TA123E | PDTC123ES | |
| PDTA123ET | SOT23 | _ | *21 ⁽¹⁾ | PDTC123ET | |
| PDTA123EU | SOT323 | SC-70 | *42 ⁽¹⁾ | PDTC123EU | |

Note

^{1. * =} p: Made in Hong Kong.

^{* =} t: Made in Malaysia.

^{* =} W: Made in China.

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

| TVDE NUMBER | CIMPLIFIED OUTLINE AND CVMPOL | | PINNING |
|--|-----------------------------------|-------|------------------------------|
| TYPE NUMBER | SIMPLIFIED OUTLINE AND SYMBOL | PIN | DESCRIPTION |
| PDTA123ES | R1 | 1 2 3 | base collector emitter |
| PDTA123EE PDTA123EEF PDTA123EK PDTA123ET PDTA123EU | Top view 1 R1 R2 R2 R2 R2 RDB271 | 1 2 3 | base emitter collector |
| PDTA123EM | 2 R1 R2 R2 RDB267 | 1 2 3 | base emitter collector |

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

ORDERING INFORMATION

| TYPE NUMBER | PACKAGE | | | | | | | | |
|-------------|------------------|---|--------|--|--|--|--|--|--|
| ITPE NUMBER | NAME DESCRIPTION | | | | | | | | |
| PDTA123EE | _ | plastic surface mounted package; 3 leads | SOT416 | | | | | | |
| PDTA123EEF | _ | plastic surface mounted package; 3 leads | SOT490 | | | | | | |
| PDTA123EK | _ | plastic surface mounted package; 3 leads | SOT346 | | | | | | |
| PDTA123EM | _ | leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm | SOT883 | | | | | | |
| PDTA123ES | _ | plastic single-ended leaded (through hole) package; 3 leads | SOT54 | | | | | | |
| PDTA123ET | _ | plastic surface mounted package; 3 leads | SOT23 | | | | | | |
| PDTA123EU | _ | plastic surface mounted package; 3 leads | SOT323 | | | | | | |

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------|--------------------------|------|------|------|
| V _{CBO} | collector-base voltage | open emitter | _ | -50 | V |
| V _{CEO} | collector-emitter voltage | open base | _ | -50 | V |
| V _{EBO} | emitter-base voltage | open collector | _ | -10 | V |
| VI | input voltage | | | | |
| | positive | | _ | +10 | V |
| | negative | | _ | -12 | V |
| Io | output current (DC) | | _ | -100 | mA |
| I _{CM} | peak collector current | | _ | -100 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | | | |
| | SOT54 | note 1 | _ | 500 | mW |
| | SOT23 | note 1 | _ | 250 | mW |
| | SOT346 | note 1 | _ | 250 | mW |
| | SOT323 | note 1 | _ | 200 | mW |
| | SOT416 | note 1 | _ | 150 | mW |
| | SOT490 | notes 1 and 2 | _ | 250 | mW |
| | SOT883 | notes 2 and 3 | _ | 250 | mW |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | _ | 150 | °C |
| T _{amb} | operating ambient temperature | | -65 | +150 | °C |

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|----------------------|---|--------------------------|-------|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | T _{amb} ≤ 25 °C | | |
| | SOT54 | note 1 | 250 | K/W |
| | SOT23 | note 1 | 500 | K/W |
| | SOT346 | note 1 | 500 | K/W |
| | SOT323 | note 1 | 625 | K/W |
| | SOT416 | note 1 | 830 | K/W |
| | SOT490 | notes 1 and 2 | 500 | K/W |
| | SOT883 | notes 2 and 3 | 500 | K/W |

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--------------------|--------------------------------------|---|------|------|------|------|
| I _{CBO} | collector-base cut-off current | $V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$ | - | _ | -100 | nA |
| I _{CEO} | collector-emitter cut-off current | $V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}$ | _ | _ | -1 | μΑ |
| | | $V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}; T_{j} = 150 ^{\circ}\text{C}$ | _ | _ | -50 | μΑ |
| I _{EBO} | emitter-base cut-off current | $V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$ | _ | _ | -2 | mA |
| h _{FE} | DC current gain | $V_{CE} = -5 \text{ V}; I_{C} = -20 \text{ mA}$ | 30 | _ | _ | |
| V _{CEsat} | collector-emitter saturation voltage | $I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$ | _ | _ | -150 | mV |
| $V_{i(off)}$ | input-off voltage | $I_C = -1 \text{ mA}; V_{CE} = -5 \text{ V}$ | _ | -1.2 | -0.5 | V |
| $V_{i(on)}$ | input-on voltage | $I_C = -20 \text{ mA}; V_{CE} = -0.3 \text{ V}$ | -2 | -1.6 | _ | V |
| R1 | input resistor | | 1.54 | 2.2 | 2.86 | kΩ |
| <u>R2</u> R1 | resistor ratio | | 0.8 | 1 | 1.2 | |
| C _c | collector capacitance | $I_E = I_e = 0 \text{ A}; V_{CB} = -10 \text{ V};$ f = 1 MHz | _ | _ | 3 | pF |

PNP resistor-equipped transistors; $R1 = 2.2 \text{ k}\Omega$, $R2 = 2.2 \text{ k}\Omega$

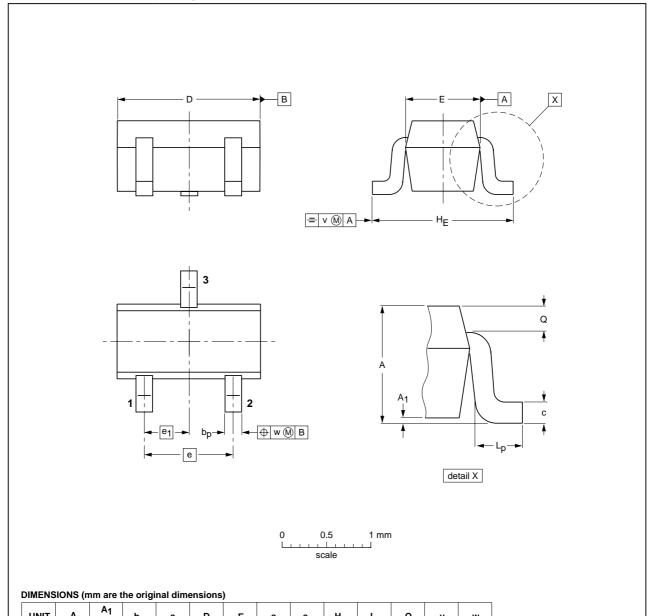
PDTA123E series

PACKAGE OUTLINES

UNIT

Plastic surface-mounted package; 3 leads

SOT416



| | | | | | | | | DEEEDE | NCES | | | | | |
|--|--|------|--|------|------|----|-----|--------|------|------|------|------|--|--|
| | | | | | | | | | | | | | | |
| ().6() (0.15 0.10 1.4 0.7 1.45 0.15 0.13 | | 0.60 | | 0.10 | 0.10 | 17 | 0.7 | | | 1.40 | 0.10 | 0.10 | | |

| OUTLINE | | REFER | ENCES | EUROPEAN | ISSUE DATE | |
|---------|-----|-------|-------|------------|----------------------------------|--|
| VERSION | IEC | JEDEC | JEITA | PROJECTION | | |
| SOT416 | | | SC-75 | | -04-11-04 06-03-16 | |

 H_{E}

 L_{p}

Q

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bp

1.8

max

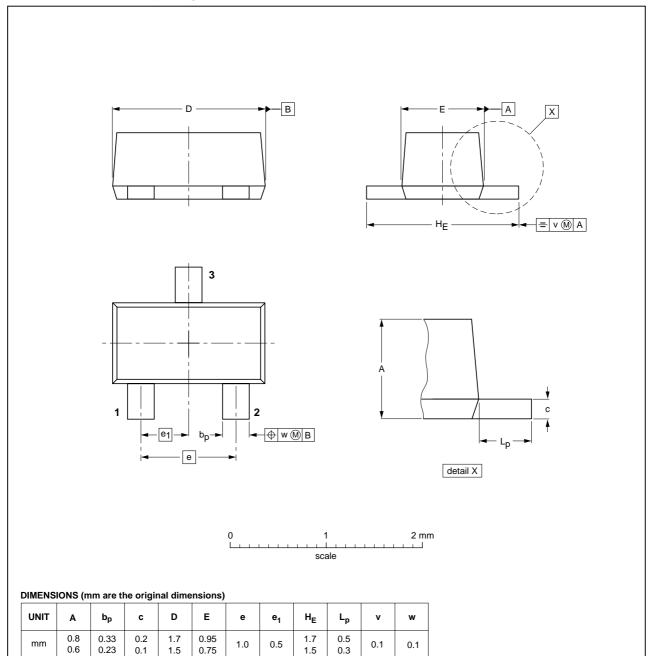
0.1

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Plastic surface-mounted package; 3 leads

SOT490



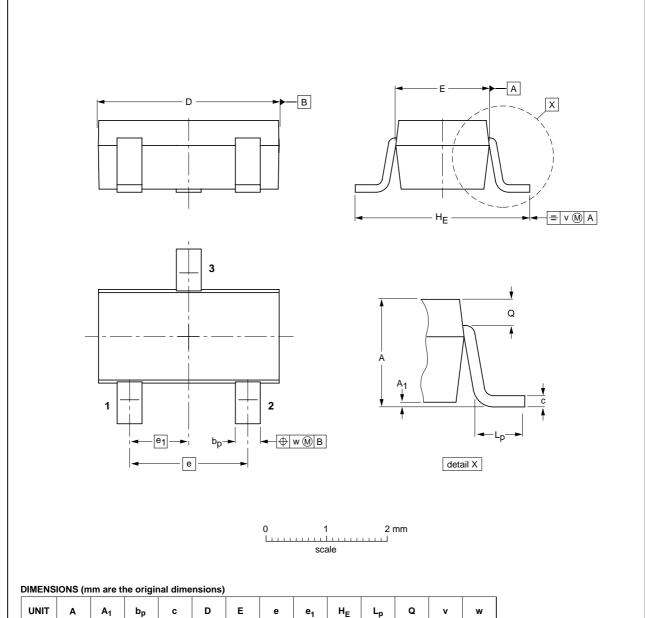
| OUTLINE | | REFER | ENCES | EUROPEAN | ISSUE DATE | | |
|---------|-----|-------|-------|------------|---------------------------------|--|--|
| VERSION | IEC | JEDEC | JEITA | PROJECTION | ISSUE DATE | | |
| SOT490 | | | SC-89 | | 05-07-28 06-03-16 | | |

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Plastic surface-mounted package; 3 leads

SOT346



| UNIT | Α | A ₁ | bp | С | D | E | е | e ₁ | HE | Lp | Q | v | w |
|------|------------|----------------|--------------|--------------|------------|------------|-----|----------------|------------|------------|--------------|-----|-----|
| mm | 1.3 1.0 | 0.1 0.013 | 0.50 0.35 | 0.26 0.10 | 3.1 2.7 | 1.7 1.3 | 1.9 | 0.95 | 3.0 2.5 | 0.6 0.2 | 0.33 0.23 | 0.2 | 0.2 |

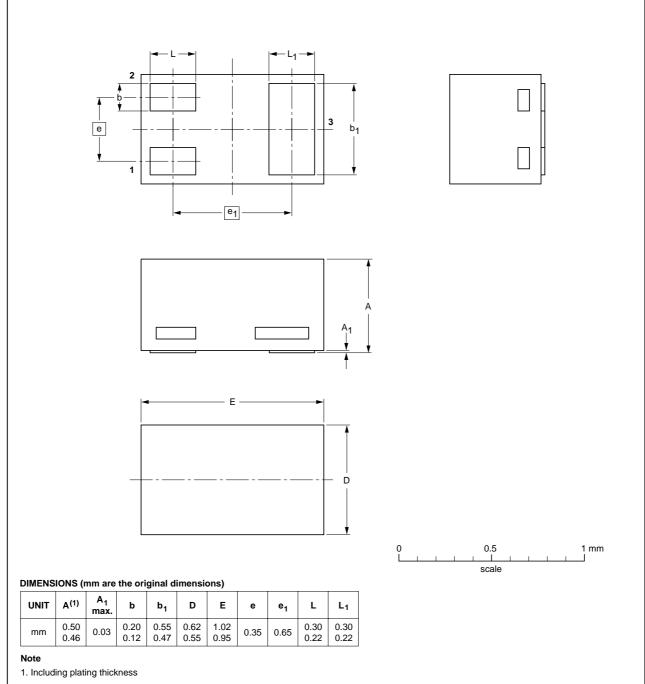
| OUTLINE | | REFER | EUROPEAN | ISSUE DATE | | | |
|---------|-----|--------|-------------|------------|------------|----------------------------------|--|
| VERSION | IEC | JEDEC | JEDEC JEITA | | PROJECTION | ISSUE DATE | |
| SOT346 | | TO-236 | SC-59A | | | -04-11-11 06-03-16 | |

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



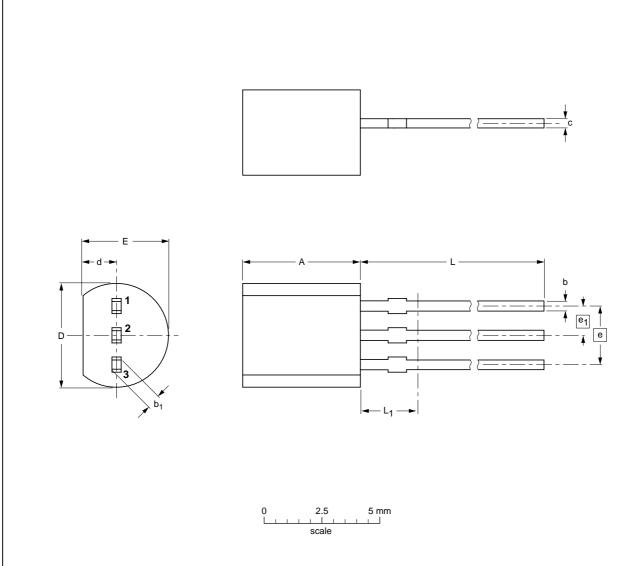
| OUTLINE | | EUROPEAN | ISSUE DATE | | | |
|---------|-----|----------|------------|--|------------|---------------------------------|
| VERSION | IEC | JEDEC | JEITA | | PROJECTION | ISSUE DATE |
| SOT883 | | | SC-101 | | | 03-02-05 03-04-03 |

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

| UNIT | Α | b | b ₁ | С | D | d | E | е | e ₁ | L | L ₁ ⁽¹⁾ max. |
|------|------------|--------------|----------------|--------------|------------|------------|------------|------|----------------|--------------|---------------------------------------|
| mm | 5.2 5.0 | 0.48 0.40 | 0.66 0.55 | 0.45 0.38 | 4.8 4.4 | 1.7 1.4 | 4.2 3.6 | 2.54 | 1.27 | 14.5 12.7 | 2.5 |

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

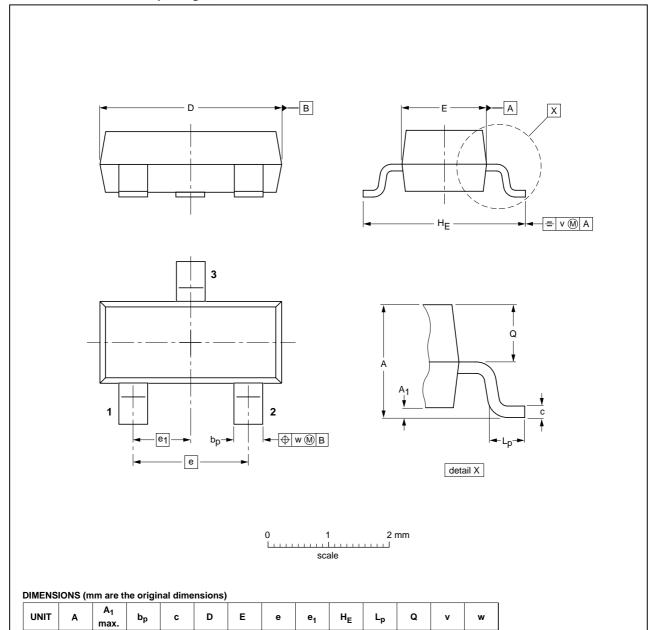
| OUTLINE | | REFER | EUROPEAN | ISSUE DATE | | |
|---------|-----|-------|----------|------------|------------|---------------------------------|
| VERSION | IEC | JEDEC | JEITA | | PROJECTION | ISSUE DATE |
| SOT54 | | TO-92 | SC-43A | | | 04-06-28 04-11-16 |

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Plastic surface-mounted package; 3 leads

SOT23



| OUTLINE | | REFER | EUROPEAN | ICCUE DATE | | | |
|---------|-------------|----------|----------|------------|------------|----------------------------------|--|
| VERSION | VERSION IEC | | JEITA | | PROJECTION | ISSUE DATE | |
| SOT23 | | TO-236AB | | | | -04-11-04 06-03-16 | |

1.9

0.45

0.55

0.2

0.1

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0.48

0.38

0.15

1.1

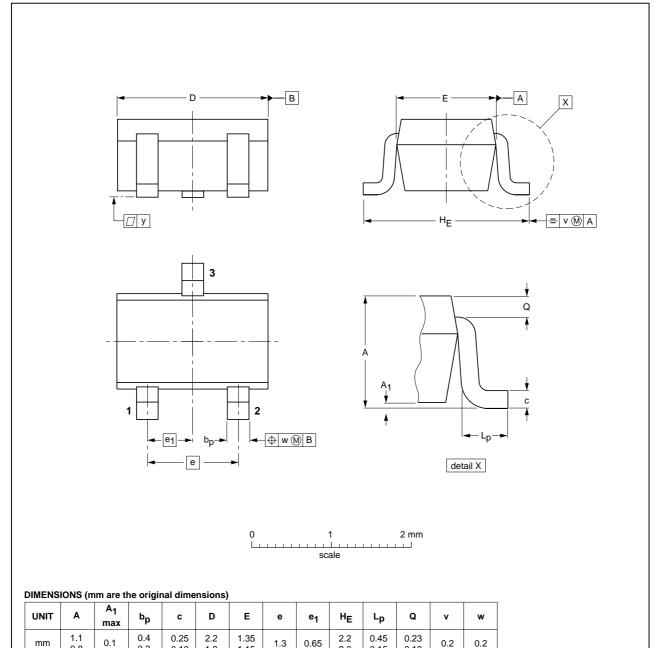
0.9

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Plastic surface-mounted package; 3 leads

SOT323



| OUTLINE | OUTLINE REFERENCES | | | | | ISSUE DATE | |
|---------|--------------------|-------|-------|--|------------|----------------------------------|--|
| VERSION | IEC | JEDEC | JEITA | | PROJECTION | ISSUE DATE | |
| SOT323 | | | SC-70 | | | -04-11-04 06-03-16 | |

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0.3

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|-----------------------------------|----------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

Notes

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